

Product Code . JA-AET-1460

Determination of Energy Band Gap in Semiconductor Diode



Description




Determination of Energy Band Gap in Semiconductor Diode

Object:

- To draw the characteristics of a P-N junction Diode for reverse saturation current and temperature
- To determine the Energy Band Gap in a P-N Junction Diode

Features:

- 2V D.C. at 10mA, regulated Power Supply
 - Digital Micro ammeter, 3½ digits having range 200mA D.C.
 - Semiconductor Diode
 - Thermometer 0-110 °C
 - Oven, Electrically heated to heat the Semiconductor Diode
 - Mains ON/OFF switch and Fuse
 - The unit is operative on 230V $\pm 10\%$ at 50Hz A.C. Mains
 - Adequate no. of patch cords stackable from rear both ends 4mm spring loaded plug length ½ metre
 - Good Quality, reliable terminal/sockets are provided at appropriate places on panel for connections /observation of waveforms
 - Strongly supported by detailed Operating Instructions, giving details of Object, Theory, Design procedures, Report Suggestions and Book References
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